Fujitsu Microelectronics Inc.
Hitachi America Ltd.
Hyundai Electronics America Inc.
IBM Microelectronics
LG Semicon America Inc.(formerly Goldstar)
Mitsubishi Electronics America Inc.
NEC Electronics Inc.
Micron Technology Inc.
Mosel Vitelic Inc.
MoSys Inc.
Oki Semiconductor
Ramtron Inc.
Samsung Semiconductor
Siemens Components Inc.
Texas Instruments, Inc.
Toshiba America Electronic Components

Fujitsu Microelectronics Inc., San Jose, Ca., 408-922-9440

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
MB81141621	SDRAM	4 MEG	2 x 128K x 16	67 MHz	134 MB/Sec	125mA	2mA	3.3 V	4Q95	$22.50 /1K	50p-TSOP/SOJ
MB81141622	SDRAM	4 MEG	2 x 128K x 16	67 MHz	134 MB/Sec	125mA	2mA	3.3 V	4Q95	$22.50 /1K	50p-TSOP/SOJ
MB81G8322	SGRAM	8 MEG	2 x 128K x 32	67 MHz	268 MB/Sec	190mA	2mA	3.3 V	1Q96	$54.00 /1K	100p-QFP
MB81G8322	SGDRAM	8 MEG	2 x 128K x 32	83 MHz	332 MB/Sec	220mA	2mA	3.3 V	1Q96	$57.00 /1K	100p-QFP
MB81G8322	SGDRAM	8 MEG	2 x 128K x 32	100 MHz	400 MB/Sec	225mA	2mA	3.3 V	1Q96	$65.00 /1K	100p-QFP
MB81116421	SDRAM	16MEG	2 x 2M x 4	67 MHz	33 MB/Sec	110mA	1mA	3.3 V	3Q95	$62.001K	44p-TSOP
	SDRAM	16MEG		83 MHz	41 MB/Sec	120mA	1mA		3Q95	65.00/1K	44p-TSOP
	SDRAM	16 MEG		100 MHz	50 MB/Sec	130mA	1mA		1Q96	TBD	44p-TSOP
MB81116422	SDRAM	16 MEG	2 x 2M x 4	67 MHz	33 MB/Sec	110mA	1mA	3.3 V	3Q95	$62.00 /1K	44p-TSOP
	SDRAM	16 MEG		83 MHz	41 MB/Sec	120mA	1mA		3Q95	$65.00 /1K	44p-TSOP
	SDRAM	16 MEG		100 MHz	50 MB/Sec	130mA	1mA		1Q96	TBD/1K	44p-TSOP
MB81116821	SDRAM	16 MEG	2 x 1M x 8	67 MHz	67 MB/Sec	110mA	1mA	3.3 V	3Q95	$68.75 /1K	44p-TSOP
	SDRAM	16 MEG		83 MHz	83 MB/Sec	120mA	1mA		3Q95	$72.00 /1K	44p-TSOP
	SDRAM	16 MEG		100 MHz	100 MB/Sec	130mA	1mA		1Q96	TBD/1K	44p-TSOP
MB81116822	SDRAM	16 MEG	2 x 1M x 8	67 MHz	67 MB/Sec	110mA	1mA	3.3 V	3Q95	$68.75 /1K	44p-TSOP
	SDRAM	16 MEG		83 MHz	83 MB/Sec	120mA	1mA		3Q95	$72.00/1K	44p-TSOP
	SDRAM	16 MEG		100 MHz	100 MB/Sec	130mA	1mA		1Q96	TBD/1K	44p-TSOP
MB811161621A	SDRAM	16 MEG	2 x 512K x 16	67 MHz	134 MB/Sec			3.3 V	1Q96	$62.50 /1K	50p-TSOP
	SDRAM	16 MEG		83 MHz	166 MB/Sec				1Q96	$65.00 /1K	50p-TSOP
	SDRAM	16 MEG		100 MHz	200 MB/Sec				1Q96	TBD/1K	50p-TSOP
MB811161622A	SDRAM	16 MEG	2 x 512K x 16	67 MHz	134 MB/Sec			3.3 V	1Q96	$62.50 /1K	50p-TSOP
	SDRAM	16 MEG		83 MHz	166 MB/Sec				1Q96	$65.00 /1K	50p-TSOP
	SDRAM	16 MEG		100 MHz	200 MB/Sec				1Q96	TBD/1K	50p-TSOP
MB81164841	SDRAM	64 MEG	4 x 2M x 8	67 MHz	67 MB/Sec	140mA	2mA	3.3 V	2H96	TBD/1K	54p-TSOP
	SDRAM	64 MEG		83 MHz	83 MB/Sec	160mA	2mA		2H96	TBD/1K	54p-TSOP
	SDRAM	64 MEG		100 MHz	100 MB/Sec	180mA	2mA		2H96	TBD/1K	54p-TSOP
MB81164842	SDRAM	64 MEG	4 x 2M x 8	67 MHz	67 MB/Sec	160mA	2mA	3.3 V	2H96	TBD/1K	54p-TSOP
	SDRAM	64 MEG		83 MHz	83 MB/Sec	170mA	2mA		2H96	TBD/1K	54p-TSOP
	SDRAM	64 MEG		100 MHz	100 MB/Sec	180mA	2mA		2H96	TBD/1K	54p-TSOP

Hitachi America Ltd., Semiconductor and IC Division, Brisbane, Ca. , 800-285-1601, Ext. 10

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
HM514405C	EDO	4M	1Mx4	40 MHz	20 MB/s	110mA	2 mA	5V	Now		20-pin SOJ 20-pin TSOP2 1K Refresh
HM514405C	EDO	4M	1Mx4	40 MHz	20 MB/s	110mA	2 mA	5V	Now		20-pin SOJ 20-pin TSOP2 1K Refresh
HM514265C	EDO	4M	256Kx16	40 MHz	80 MB/s	150	2	5V	Now		40-pin SOJ 512 Refresh
HM51W4265C	EDO	4M	256Kx16	40 MHz	80 MB/s	150	2	3.3V	Now		40-pin TSOP2 512 Refresh
HM5117805B	EDO	16M	2Mx8	40 MHz	40 MB/s	120	2	5V	Now		28-pin SOJ 28-pin TSOP2 2K Refresh
HM51W17805B	EDO	16M	2Mx8	40 MHz	40 MB/s	120	2	3.3V	Now		28-pin SOJ 28-pin TSOP2 2K Refresh
HM5118165A	EDO	16M	1Mx16	40 MHz	80 MB/s	150	2	5V	Now		42-pin SOJ 44-pin TSOP2 1K Refresh
HM51W18165A	EDO	16M	1Mx16	40 MHz	80 MB/s	150	2	3.3V	Now		42-pin SOJ 44-pin TSOP2 1K Refresh
HM51W16165A	EDO	16M	1Mx16	40 MHz	80 MB/s	100	2	3.3V	Now		42-pin SOJ 44-pin TSOP2 4K Refresh
HM5221605	SDRAM	2M	64Kx16x2	80 MHz	160 MB/s	85	3	3.3V	Now		50-pin TSOP2 2 Banks
HM5241605	SDRAM	4M	128Kx16x2	80 MHz	160 MB/s	95	3	3.3V	Now		50-pin SOJ 50-pin TSOP2 2 Banks
HM5283206	SGDRAM	8M	128Kx32x2	100 MHz	400 MB/s	160	3	3.3V	Q4'95		100-pin PQFP 2 Banks
HM5216405	SDRAM	16M	2Mx4x2	100 MHz	50 MB/s	100	3	3.3V	Q4'95		44-pin TSOP2 2 Banks
HM5216805	SDRAM	16M	1Mx8x2	100 MHz	100 MB/s	100	3	3.3V	Q4'95		44-pin TSOP2 2 Banks
HM5216165	SDRAM	16M	512Kx16x2	100 MHz	200 MB/s	130	3	3.3V	Q4'95		50-pin TSOP2 2 Banks

Hyundai Electronics America Inc., San Jose, Ca. 408-232-8338

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
HY512264	EDO	2M	128Kxl6	50/60/70 ns 50MHz				5.0	2Q 96		40pin SOJ 40/44 pin TSOP
HY514264B		4M	256kx16	50/60/70 50MHz				5.0	NOW		40pin SOJ 40/44 pin TSOP
HY5lV4264B		4M	256Kxl6	6O/7O/8O 41.6 MHz				3.3	NOW		40pin SOJ 40/44 pin TSOP
HY5116404A		16M	4Mx4 4k ref	60/70/80 40MHz				5.0	NOW		24/26pin SOJ 24/25 pin TSOP
HY5lVl6404A			4Mx4 4k ref	60/70/80 40MHz				3.3	NOW		24/26pin SOJ 24/26 oin TSOP
HY5117404A			4Mx4 2k ref	60/70/80 40MHz				5.0	NOW		24/26pin SOJ TSOP
HYlVl7404A			4Mx4 2k ref	60/70/80 40 MHz				3.3	Nov.95		24/26pin SOJ TSOP
HY5116404B			4Mx4 4k ref	50/60/70 50MHz				5.0	2Q 96		24/26pin SOJ TSOP
HY5lVl6404B			4Mx4	6O/7O/8O 40MHz				3.3	2Q 96		24/26 pin SOJ TSOP
HY5117404B			4Mx4 2k ref	50/60/70 50MHz.				5.0	2Q 96		24/26 pin SOJ
HY5lVl7404B.			4Mx4 2k ref	60/70/80 40MHz				3.3	2Q/96		24/26pin SOJ TSOP
HY5116164B			lMx16 4k ref	60/70/80 4OMHz				5.0	Jan.96		42pin SOJ 44/50 PIN TSOP
HY5lVl6l64B			lMxl6 4kref	60/70/80 40MHz				3.3	Dec.95		42pin SOJ 44/50 PIN TSOP
HY5118164B			lMxl6 4kref	60/70/80 40MHz				5.0	Jan.96		42pin SOJ 44/50 PIN TSOP
HY51VI8164B			lMxl6 1kref	60/70/80 40MHz				3.3	Feb.96		42pin SOJ 44/50 PIN TSOP
HY1V17405B	BEDO	16M	4Mx4 2kref	50/60/70 66.6MHz				3.3	2Q 96		24/26pin SOJ 24/26 pin TSOP
HY5lVl7805B			2Mx8 2k ref	50/60/70 66.6MHz				3.3	2Q 96		28pin SOJ 28 pin TSOP
HY5lVl8l65B			lMxl6 1k ref	50/60/70 66.6MHz				3.3	2Q 96		42 pin SOJ 44/50 PIN TSOP
HY57Vl6401TC	SDRAM	16M	4MX4	10/12/15	100MB/s			3.3	2Q 96		44 pin TSOP II 400mil
HY57Vl6801TC			2Mx8	10/12/l5	100MB/s			3.3	2Q 96.		44 pin TSOP II 400mil
HY57Vl6l6lTC			lMxl6	10/12/15	100MB/s			3.3	2Q 96		64 pin TSOP II 400mil
HY5216256GE	VRAM	4M	256Kx16	60/70/80 33.3MHz(EDO)				5.0	2Q 96		64 PIN 525 mil SSOP
HY5216257GE			256Kx16	60/70/80 33.3MHz(EDO)				5.0	2Q 96		64 pin 525 mil SSOP
HY588321 QF	SGDRAM	16M	256Kx32	10/12/15 100MHz	100MB/s			3.3	2Q 97		100 pin QFP
HY588321 TC			256Kx32	10/11	100MB/s			3.3	2Q 97		80 pin400 mil TSOP

IBM Microelectronics, Mt. Prospect, Ill. 800-426-0181 or 802-759-7644

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
IBM0116405PT1D-60	EDO DRAM	16Mb	4M x 4	60ns		40	85 mA	3.3V	NOW	N/A	.300 inch TSOP 26/24 pins Low Power Self Refresh
IBM0116405PT1D-70	EDO DRAM	16Mb	4M x 4	70ns		33	75	3.3V	NOW	N/A	.300 TSOP 26/24 pin Low Power Self Refresh
IBM0116405J1D-60	EDO DRAM	16Mb	4M x 4	60ns		40	85	5.0V	NOW	N/A	.300 SOJ 26/24 pin
IBM0116405J1D-70	EDO DRAM	16Mb	4M x 4	70ns		33	75	5.0V	NOW	N/A	.300 SOJ 26/24 pin
IBM117405J!D-60	EDO DRAM	16Mb	4M x 4	60ns		40	125	5.0V	NOW	N/A	.300 SOJ 26/24 pin
IBM117405J!D-70	EDO DRAM	16Mb	4M x 4	70ns		33	110	5.0V	NOW	N/A	.300 SOJ 26/24
IBM0116405BT1D-60	EDO DRAM	16Mb	4M x 4	60ns		40	85	3.3V	NOW	N/A	.300 TSOP 26/24
IBM0116405BT1D-70	EDO DRAM	16Mb	4M x 4	70ns		33	75	3.3V	NOW	N/A	.300 TSOP 26/24
IBM117805PT3D-60	EDO DRAM	16Mb	2M x 8	60ns		40	125	3.3V	NOW	N/A	.400 TSOP 28/28 Low Power Self Refresh
IBM117805PT3D-70	EDO DRAM	16Mb	2M x 8	70ns		33	110	3.3V	NOW	N/A	.400 TSOP 28/28 Low Power Self Refresh
IBM117805T3D-60	EDO DRAM	16Mb	2M x 8	60ns		40	125	5.0V	NOW	N/A	.400 TSOP 28/28
IBM117805T3D-70	EDO DRAM	16Mb	2M x 8	70ns		33	110	5.0V	NOW	N/A	.400 TSOP 28/28
IBM117805BT3D-60	EDO DRAM	16Mb	2M x 8	60ns		40	125	3.3V	NOW	N/A	.400 TSOP 28/28
IBM117805BT3D-70	EDO DRAM	16Mb	2M x 8	70ns		33	110	3.3V	NOW	N/A	.400 TSOP 28/28
IBM116165PT3D-60	EDO DRAM	16Mb	1M x 16	60ns		40	85	3.3V	NOW	N/A	.400 TSOP 50/44 Low Power Self Refresh
IBM116165PT3D-70	EDO DRAM	16Mb	1M x 16	70ns		33	75	3.3V	NOW	N/A	.400 TSOP 50/44 Low Power Self Refresh
IBM118165PT3D-60	EDO DRAM	16Mb	1M x 16	60ns		40	205	3.3V	NOW	N/A	.400 TSOP 50/44 Low Power Self Refresh
IBM118165PT3D-70	EDO DRAM	16Mb	1M x 16	70ns		33	180	3.3V	NOW	N/A	.400 TSOP 50/44 Low Power Self Refresh
IBM116165T3D-60	EDO DRAM	16Mb	1M x 16	60ns		40	85	5.0V	NOW	N/A	.400 TSOP 50/44
IBM116165T3D-70	EDO DRAM	16Mb	1M x 16	70ns		33	75	5.0V	NOW	N/A	.400 TSOP 50/44
IBM118165T3D-60	EDO DRAM	16Mb	1M x 16	60ns		40	205	5.0V	NOW	N/A	.400 TSOP 50/44
IBM118165T3D-70	EDO DRAM	16Mb	1M x 16	70ns		33	180	5.0V	NOW	N/A	.400 TSOP 50/44
IBM116165BT3D-60	EDO DRAM	16Mb	1M x 16	60ns		40	85	3.3V	NOW	N/A	.400 TSOP 50/44
IBM116165BT3D-70	EDO DRAM	16Mb	1M x 16	70ns		33	75	3.3V	NOW	N/A	.400 TSOP 50/44
IBM118165BT3D-60	EDO DRAM	16Mb	1M x 16	60ns		40	205	3.3V	NOW	N/A	.400 TSOP 50/44
IBM118165BT3D-70	EDO DRAM	16Mb	1M x 16	70ns		33	180	3.3V	NOW	N/A	.400 TSOP 50/44
IBM0316409C-10	Sync DRAM	16Mb	4M x 4	9 ns 100MHz		100	55	3.3V	1Q96	N/A	.400 TSOP 44 Self Refresh
IBM0316409C-11	Sync DRAM	16Mb	4M x 4	10 ns 91MHz		41	50	3.3V	1Q96	N/A	.400 TSOP 44 Self Refresh
IBM0316409C-12	Sync DRAM	16Mb	4M x 4	11 ns 83MHz		83	45	3.3V	1Q96	N/A	.400 TSOP 44 Self Refresh
IBM0316409C-13	Sync DRAM	16Mb	4M x 4	12 ns 75MHz		75	40	3.3V	1Q96	N/A	.400 TSOP 44 Self Refresh
IBM0316809C-10	Sync DRAM	16Mb	2M x 8	9 ns 100MHz		100	60	3.3V	1Q96	N/A	.400 TSOP 44 Self Refresh
IBM0316809C-11	Sync DRAM	16Mb	2M x 8	10 ns 91MHz		41	55	3.3V	1Q96	N/A	.400 TSOP 44 Self Refresh
IBM0316809C-12	Sync DRAM	16Mb	2M x 8	11 ns 83MHz		83	50	3.3V	1Q96	N/A	.400 TSOP 44 Self Refresh
IBM0316809C-13	Sync DRAM	16Mb	2M x 8	12 ns 75MHz		75	45	3.3V	1Q96	N/A	.400 TSOP 44 Self Refresh
IBM0316169C-10	Sync DRAM	16Mb	1M x 16	9 ns 100MHz		100	70	3.3V	1Q96	N/A	.400 TSOP 50 Self Refresh
IBM0316169C-11	Sync DRAM	16Mb	1M x 16	10 ns 91MHz		41	65	3.3V	1Q96	N/A	.400 TSOP 50 Self Refresh
IBM0316169C-12	Sync DRAM	16Mb	1M x 16	11 ns 83MHz		83	55	3.3V	1Q96	N/A	.400 TSOP 50 Self Refresh
IBM0316169C-13	Sync DRAM	16Mb	1M x 16	12 ns 75MHz		75	50	3.3V	1Q96	N/A	.400 TSOP 50 Self Refresh
IBM025160LG5D-60	VRAM	4Mb	256K x 16	60ns			160	5.0V	NOW	N/A	.472 SSOG 64 Fast Page w/2CE
IBM025160LG5D-70	VRAM	4Mb	256K x 16	70ns			150	5.0V	NOW	N/A	.472 SSOG 64 Fast Page w/2CE
IBM025161LG5D-6H	VRAM	4Mb	256K x 16	<60ns 50MHz (EDO)			160	5.0V	NOW	N/A	.472 SSOG 64 EDO w/2CE
IBM025161LG5D-60	VRAM	4Mb	256K x 16	60ns			160	5.0V	NOW	N/A	.472 SSOG 64 EDO w/2CE
IBM025161LG5D-70	VRAM	4Mb	256K x 16	70ns			150	5.0V	NOW	N/A	.472 SSOG 64 EDO w/2CE
IBM025170LG5D-60	VRAM	4Mb	256K x 16	60ns			160	5.0V	NOW	N/A	.472 SSOG 64 Fast Page2WE
IBM025170LG5D-70	VRAM	4Mb	256K x 16	70ns			150	5.0V	NOW	N/A	.472 SSOG 64 Fast Page w/2WE
IBM025171LG5D-6H	VRAM	4Mb	256K x 16	<60ns 50MHz (EDO)			160	5.0V	NOW	N/A	.472 SSOG 64 EDO w/2WE
IBM025171LG5D-60	VRAM	4Mb	256K x 16	60ns			160	5.0V	NOW	N/A	.472 SSOG 64 EDO w/2WE
IBM025171LG5D-70	VRAM	4Mb	256K x 16	70ns			150	5.0V	NOW	N/A	.472 SSOG 64 EDO w/2WE
IBM025160NG5D-60	VRAM	4Mb	256K x 16	60ns			150	3.3V	NOW	N/A	.472 SSOG 64 Fast Page w/2CE
IBM025160NG5D-70	VRAM	4Mb	256K x 16	70ns			140	3.3V	NOW	N/A	.472 SSOG 64 Fast Page w/2CE
IBM025161NG5D-6H	VRAM	4Mb	256K x 16	<60ns 50MHz (EDO)			150	3.3V	NOW	N/A	.472 SSOG 64 EDO w/2CE
IBM025161NG5D-60	VRAM	4Mb	256K x 16	60ns			150	3.3V	NOW	N/A	.472 SSOG 64 EDO w/2CE
IBM025161NG5D-70	VRAM	4Mb	256K x 16	70ns			140	3.3V	NOW	N/A	.472 SSOG 64 EDO w/2CE
IBM025170NG5D-60	VRAM	4Mb	256K x 16	60ns			150	3.3V	NOW	N/A	.472 SSOG 64 Fast Page w/2WE
IBM025170NG5D-70	VRAM	4Mb	256K x 16	70ns			140	3.3V	NOW	N/A	.472 SSOG 64 Fast Page with 2WE
IBM025171NG5D-6H	VRAM	4Mb	256K x 16	<60ns 50MHz (EDO)			150	3.3V	NOW	N/A	.472 SSOG 64 EDO with 2WE
IBM025171NG5D-60	VRAM	4Mb	256K x 16	60ns			150	3.3V	NOW	N/A	.472 SSOG 64 EDO with 2WE
IBM025171NG5D-70	VRAM	4Mb	256K x 16	70ns			140	3.3V	NOW	N/A	.472 SSOG 64 EDO with 2WE
IBM088329NG6A-10	SGRAM	8Mb	256K x 32	9ns 100MHz		400		3.3V	3Q96	N/A	.65mm lead pitch LQFP 100
IBM088329NG6A-12	SGRAM	8Mb	256K x 32	11ns 83MHz		332		3.3V	3Q96	N/A	.65mm lead pitch LQFP 100
IBM088329NG6A-15	SGRAM	8Mb	256K x 32	13ns 66MHz		264		3.3V	3Q96	N/A	.65mm lead pitch LQFP 100

LG Semicon America Inc.(formerly Goldstar), San Jose, Ca., 408-432-5000

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
GM71C4263A	EDO	4M	256K x 16	60NS				5V	4Q'95 SAMPLING		2 CAS 40 PIN SOJ
GM71C4173A	EDO	4M	256K x 16	60NS				5V	4Q'95 SAMPLING		2 WE 512/1K REFRESH 40 PIN SOJ
GM71C16163A	EDO	16M	1M x 16	60NS				5V	4Q'95 SAMPLING		1KX4K REFRESH 42 PIN SOJ
GM71V16163A	EDO	16M	1M x 16	60NS				3.3V	4Q'95 SAMPLING		1K/4K REFRESH 42 PIN SOJ
GM72V16821T	SDRAM	16M	2M x 8	66MHZ				3.3V	SAMPLING 1Q'96		2 BANKS 44 PIN TSOP II LVTTL INTERFACE
GM72V16822T	SDRAM	16M	2M x 8	100MHZ				3.3V	SAMPLING 1Q'96		44 PIN TSOP II CTT INTERFACE 2 BANKS
GM73V8800A	RDRAM	16M	1M x 8		533MB/SEC			3.3V	SAMPLING 1Q'96		32 PIN SHP
GM73C16800A	RDRAM	16M	2M x 8		533MB/SEC			5V	SAMPLING 3Q'96		32 PIN SVP/SHP
GM73V16800A	RDRAM	16M	2M x 8		533MB/SEC			3.3V	SAMPLING 3Q'96		32 PIN SVP/SHP

Mitsubishi Electronics America Inc., Sunnyvale, Ca., 408-730-5900

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
MSM4V4169	Cached DRAM	4Mb	256k x 16	15ns100Mhz	100 to 200MB/sec at 66 to 100 MHz			3.3+/-O.3V	Now	$16.00/1000	TSOP/Reverse TSOP Programmable burst 16M
MSM4V16169	Cached DRAM	16Mb	1M x 16	10 ns100Mhz	100 to 200MB/sec at 66 to 100MHz			3.3+/-O.3V	Now	$65.00/1000	TSOP/Reverse TSOP Programmable burst 16M
MSM44265C	EDO DRAM (Hyper Page)	4Mb	256k x 16	25 ns50MHz	80 to 100MB/sec at 40 to 50 MHz			5V+/-10%	Now	$17.00/100	44-pin TSOP/40-pin SOJ
M5M4V18165B	EDO DRAM (Hyper Page)	16Mb	1M x 16	25ns 50 MHz	80 to 100MB/sec at 40 to 50 MHz			3.3+/-0.3V	Now	$65.00/1000	50-pin TSOP/42-pin SOJ
MSM410092	3D-DRAM	10Mb	N/A	10 ns 100 MHz	400MB/sec at 100MHz			3.3V+/-5%	Now	$96.00/1000	QFP Fine Pitch 4 interleaved banks of DRAM on-chip ALU 2Kb on-board pixel buffer dual video buffers
M5M4V16407A	Synchronous DRAM	16Mb	4M x 4	10ns 100 MHz	100 to 200 MB/sec at 100MHz			3.3+/-0.3V	Now	$77.00/1000	TSOP pinout TBD Dual banks of DRAM JEDEC standard
M5M4V16807A	Synchronous DRAM.	16Mb	2M x 8	10 ns 100 MHz	100 to 200MB/sec at 100 MHz			3.3+/-0.3V	Now	$77.00/1000	TSOP/ pinout TBD Dual banks of DRAM JEDEC standard

NEC Electronics Inc., Mountain View, Ca. 800-366-9782

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
uPD4216405	Hyper-Page Mode DRAM (aka EDO DRAM)	16 Mb	4M x 4	50/40/33 MHz 50/60/70 ns				5 V			26-pin TSOP/SOJ
uPD12S16805	HPM DRAM	16 Mb	2M x 8	50/40/33 MHz 50/60/70 ns				5V			28-pin TSOP/SOJ
uPD42S16165	HPM DRAM	16 Mb	1M x 16	50/40/33 MHz 50/60/70 ns				5V			TSOP/SOJ
uPD42S18165L	HPM DRAM	16 Mb	1M x 16	50/40/33 MHz 50/60/70 ns				3.3 v			TSOP/SOJ
uPD42S17805	HPM DRAM	16 Mb	2M x 8	50/40/33 MHz 50/60/70 ns				5V			TSOP/SOJ
uPD42S17805L	HPM DRAM	16 Mb	2M x 8	50/40/33 MHz 50/60/70 ns				3.3 V			TSOP/SOJ
uPD42S16165	HPM DRAM	16 Mb	1M x 16	50/40/33 MHz				5V			TSOP/SOJ
uPD42516165L	HPM DRAM	16 Mb	1M x 16	40/33 MHz 60/70 ns				3.3 V			50-pin TSOP, 42 pin SOJ
uPD42S18165L	HPM DRAM	16 Mb	1M x 16	50/40/33 MHz 50/60/70 ns				3.3 V			TSOP
uPD42S4805A	HPM DRAM	4M	512K x 8	50/40/33 MHz 50/60/70 ns				5V			28-pin TSOP/SOJ
uPD42S4210	HPM DRAM	4M	256K x 16	50/60/33 MHz 50/60/70 ns				5V			44-pin TSOP, 40 pin SOJ
uPD482445	HPM DRAM	4M	256K x 16	33/28/25 MHz 60/70/80 ns				5V			64-pin shrink SOP 70-pin TSOP
uPD4516421/ 821/161	Synchronous DRAM	16 Mb	2Mx4x2 / 1Mx8x2 / 512Kx16x2	100 MHz	100 MB/s			3.3 V			TSOP (44-pin: x4 x8) (50-pin: x16)
uPD188170L	Rambus DRAM	18 Mb	2M x 9	250 MHz	500 MB/s			3.3 V			32-pin SSOP/SVP
uPD488130L	Rambus DRAM	16 Mb	2M x 8	250 MHz	500 MB/s			3.3 V			32-pin SSOP/SVP
uPD48830L	Rambus DRAM	8M	1M x 8	250 MHz	500 MB/s			3.3 V			32-pin SSOP/SVP
uPD482235-60/70/80 ns	Dual-Port Graphics Buffer	2M	256K x 8	33/28/25 MHz 60/70/80 ns				5V			44 pin TSOP 40-pin SOJ HPM
uPD481850	Synchronous Graphics DRAM	8M	128K x 32 bits x 2 banks	100 MHz	100 MB/s			3.3 V			100-pin QFP

Micron Technology Inc., Boise, Idaho 208- 368-3950

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
MT4C1004 MT4C4001 MT4C4004 MT4C4007 MT4C16257 MT4C16270	EDOBURSTEDO	4 Mb	4M x 1 (FP) 1 Meg x 4 (FP) 1 Meg x 4 (EDO) 256K x16 (FP) 256K x 16 (EDO)	FP 25 MHz EDO 40 MHz	80 Mbytes/s			5V	Now	Market Price	SOJ TSOP EDO 256K x 16 in Q4 95
MT4LC4M4B1/E8/G6 MT4LC2M8B1/E7/F4 MT4LC1M16C3/E5/H5	EDOBURSTEDO	16 Mb	4 M x 4 2 M x 8	FP(25 MHz) EDO(40MHz) Burst EDO(75 MHz)	150 MBytes/sec			3.3V	Now	Market price	SOJ TSOP
MT4LC256K32D4	SGDRAM	8 Mbit	256K x 32	100 MHz	400 Mbytes/sec			3.3V	Smpl 4Q 95	TBA	100 pin TQFP
MT4LC16M4 MT4LC 8M8 MT4LC4M16	EDO Burst EDO FP	64 Meg	4 M x 16 8 M x 8 16 M x 4	75 MHz	150 Mbytes/s			3.3V	Samples Now	Market Price	34 pin SOJ

Mosel Vitelic Inc., San Jose, CA 408-433-6000, FAX: 408-433-0952

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
V53C8258H	EDO/Fast Page Mode	2M	256k x 8	45ns RAS20 ns EDO	50 (per 8-bits bus-width)	800 (fpm)475 (EDO)		5 V	Now	$10.00/1000	24-PDIP, 24/26- SOJStd. 3.3-V Capable
V53C16258H	EDO/fpm	4M	256k x 16	50 ns RAS 22 ns EDO	90 (per 16-bits bus-width)	1000		5 V	Now	$20.00/10K	40-SOJ 3.3-V Capable

MoSys Inc., San Jose, CA   Phone: 408-321-0777 Fax: 408-321-0780

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
MD908AJ-166-5	Multibank DRAM	4Mbit to 18 Mbit	128Kx32 to 576Kx32	166 MHz	666 MBytes/sec			5v only or 5V/3.3V I/O	Now	$33/MByte	68 PLCC/128 PQFP 26 Signal Low Swing CMOS Interface

Oki Semiconductor, Sunnyvale, Ca. 408-720-1900

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
MSM56V16400	SDRAM	16M	4Mx4	100MHz	50MB/s			3.3V	Samples Now Production Q1 96	N/A	44 pin TSOP. Strip version. coming
MSM56V16800	SDRAM	16M	2Mx8	100MHz	100MB/s			3.3V	Samples Now Production Q1 96	N/A	44 pin TSOP
MSM56V16160	SDRAM	16M	1Mx16	100MHz	200MB/s			3.3V	Q4/95 amples Q2/96 Production	N/A	50 pin TSOP
MSM541612x	Graphic EDO	2M	128Kx16	50ns 37MHz	74MB/s			5V	Samples Now Prodctn Jan./96	Around $11	40 pin SOJ. Burst available also
MSM5416257A	Burst DRAM	4M	256Kx16	50ns 80MHz	160MB/s			5V/(3.3V)	Samples Now Prodctn Jan./96	10~15%over EDO	40 pin SOJ Same as 256Kx16 EDO
MSM5416258A	EDO	4M	256Kx16	50ns 50 MHz	100MB/s			5V/(3.3V) .	Now Samples Production Jan 96	N/A	40 pin SOJ
MSM541626x	VRAM	4M	256Kx16/512x16	50ns 50MHz (SAM)	100MB/s (SAM)	.		5V/(3.3V)	Now Samples	$22~$25	64 pin SSOP/ 70 pin TSOP
MSM541627x	VRAM	4M	256Kx16/512x16	50ns 50MHz(SAM)	100MB/s (SAM)			5V/(3.3V)	Samples Now. Jan./96 Production	$22~$25	64 pin SSOP 70 pin TSOP 2 CAS
MSM5432128	Graphic EDO	4M	128kx32	40ns45 MHz	180 Mb/s			5V	Sept./95 samples, Jan 96, Prodiction	256Kx16+15~20%	64 pin SSOP 70 pin TSOP
MSM54V32128	Graphic EDO	4M	128Kx32	50ns35 MHz	140MB			3.3V	Samples Now, Jan 96 production	256Kx16+20%	64 pin SSOP70 pin TSOP
MSM5432256	Graphic Burst EDO	8M	256Kx32	50ns80 MHz	320MB			5V/(3.3V)	Q2/96 samplesQ3/96 production	TBD	64 pin SSOP 70 pin TSOP
MSM54V25632	SGRAM	8M	256Kx32	83MHz	332MB			3.3 V	Q2/96 samplesQ3/96 production	TBD	100 pinQFP
MSM541222	EIEO	2M	256Kx12	25ns25MHz	25MB			5V	Q4/95 samples Q1 96 prod.uction	TBD	TBD

Ramtron Inc. Colorado Springs, 719-481-7000, Fax: 719-488-9095

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
DM2200	EDRAM	4Mbit	4Mx1	125 Mhz	1GB/sec			+5 v	Now	$17(100k)	SOJ 28 pin 15ns cache 35 ns row access 8 ns nibble mode
DM2202	EDRAM	4Mbit	1Mx4	66 Mhz	528 MB/sec.			+5 volt	Now	$17(100K)	SOJ 28-pin 15 ns cache 35 ns row access TSOP 44-pin
DM2212	EDRAM	4Mbit	1Mx4	66 Mhz	528 MB/sec			+5 volt	Now	$17(100K)	SOJ 28-pin 15 ns cache 35 ns row access Write-per-bit
DM2203	EDRAM	4Mbit	512Kx8	66 Mhz	528 MB/sec			+5 volt	4Q95	$20(100K)	TSOP 44-pin 4-15 ns caches 35 ns row access EDO Hit Pin
DM2213	EDRAM	4Mbit	512Kx8	66 Mhz	528 MB/sec			+5 volt	4Q95	$20(100K)	TSOP 44-pin 4-15 ns caches 35 ns row access EDO Hit Pin Write-per-bit
DM2223	EDRAM	4Mbit	512Kx8	66 Mhz	528 MB/sec			+5 volt	4Q95	$20(100K)	TSOP 44-pin 4-15 ns caches 35 ns row access Burst EDO
DM2233	EDRAM	4Mbit	512Kx8	66 Mhz	528 MB/sec			+5 volt	4Q95	$20(100K)	TSOP 44-pin 4-15 ns cache 35 ns row access Burst EDO Write-per-bit
DM1M32	EDRAM	4MByte	1Mx32	66 Mhz	528 MB/sec			+5 volt	Now	$148(100K)	SIMM 72-pin 15 ns cache 35 ns row access
DM1M36	EDRAM	4MByte	1Mx36	66 Mhz	528 MB/sec			+5 volt	Now	$165(100K)	SIMM 72-pin 15 ns cache 35 ns row access Write-per-bit Parity
DM2M32	EDRAM	8MByte	2Mx32	66 Mhz	528 MB/sec			+5 volt	Now	$296(100K)	SIMM 72-pin 15 ns cache 35 ns row access
DM2M36	EDRAM	8MByte	2Mx36	66 Mhz	528 MB/sec			+5 volt	Now	$330(100K)	SIMM 72-pin 15 ns cache 35 ns row access Write-per-bit Parity
DM4M32	EDRAM	16 Mbyte	4Mx32	125 Mhz	1 GB/sec			+5 volt	4Q95	$578(100K)	SIMM 72-pin 15 ns cache 35 ns row access 8 ns nibble mode

Samsung Semiconductor, San Jose, Ca. 408-954-7000

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
KM48C124	EDO	1Mb	128Kx8	60/70 ns	40	70	1	5	2/96	N/A	
KM416C64			64Kx16	60/70	80	80	1	5	2/96	N/A	
KM416C254B		4Mb	256Kx16	50/60/70	100	90	1	5	Now	N/A	
KM416V254B			256Kx16	60/70	80	70	0.5	3.3	Now	N/A	
KM44C4004A		16Mb	4Mx4	50/60/70	25	90	1	5	Now	N/A	4KRef
KM44C4104A			4Mx4	50/60/70	25	100	1	5	Now	N/A	2KRef
KM48C2104A			2Mx8	50/60/70	50	100	1	5	Now	N/A	2KRef
KM416V1O04A			1Mx16	60/70	80	100	1	5	Now	N/A	4KRef
KM416C1204A			1Mx16	60/70 ns	80	160	1	5	Now	N/A	1kRef
KM44V4004A			4Mx4	60/70 ns	20	80	1	3.3	Now	N/A	4kRef
KM44V4104A			4Mx4	60/70	20	100	1	3.3	Now	N/A	2KRef
KM48V2104A			2Mx8	60/70	40	100	1	3.3	Now	N/A	2KRef
KM 416V1004A			1Mx16	60/70	80	90	1	3.3	Now	N/A	4k Ref
KM 46V1204A			1Mx16	60/70	80	150	1	3.3	Now	N/A	1KRef
KM44V16004A		64Mb	16Mx4	50/60/70	25	90	0.5	3.3	Q1 96	N/A	8kRef
KM44V16104A			16Mx4	50/60/70	25	140	0.5	3.3	Q1 96	N/A	4k Ref
KM48V8004A			8Mx8	50/6O/7O	50	90	0.5	3.3	Ql96	N/A	8KRef
KM48V8l04A				50/60/70	50	140	0.5	3.3	Ql96	N/A	8KRef
KM44S4020AT-G	Synch Dram	16 Mb	4Mx4	10/12/13 ns	50	120	2	3.3	Now	N/A	4K Ref LVTTL
KM48S2020			2Mx8	10/12/13	100	125	2	3.3	Now	N/A	4KRef. LVTTL
KM416S1120AT-G			1Mx16	10/12/13	200	170	2	3.3	Now	N/A	2K Ref. LVTTL
KM4216C256-60/70KM4216C258G-60/70	Video RAM	4Mb	256kx16 DRAM port, 512x16 SAM	40 MHz60/70 ns	80 MB/sec	-------	------	5 3.3	Now	N/A	8 Col block write, EDO,64 pin SSOP
KM4232W259Q-60/70	Window RAM	8Mb	256kx32 DRAM, 128x16 SAM	50MHz60/70 ns	200 MB/sec			5	Now	N/A	120 pin PQFQ
KM132G271Q10/12/13	SGDRAM	8Mb	256K X32	100MHz10/12/13 ns	322 MB/sec			3.3	Now	N/A	dual bank, pulsed RAS , LVTTL, 3 CAS latency,

Siemens Components Inc., Integrated Circuits Division, Cupertino, Ca.., 408-777-4546

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
HYB 514175BJ/BJL-50/-60	EDO (Hyper Page Mode)	4M	256kxl6	Min. R/W Cycle Time 84ns (-50) 104ns (-60) HPM (EDO) Cycle time 20ns (-50) 25ns (-60)	100MB/s (-50) 80MB/s (-60)			5V+/-0%	Samples - Q4 95; Volume - Q1 96	N/A	P-SOJ-40 400 Mils JEDEC Standard
HYB 5116405BJ/BT-50/-60/-70 HYB 5117405BJ/BT-50/-60/-70	EDO w/4k refresh (6405) or 2k refresh (7405)	16M	1Mx16	Min. R/W Cycle Time 84ns (-50) 104ns (-60) 124ns (-70) HPM (EDO) Cycle Time 20ns (-50) 25ns (-60) 30ns (-70)	25MB/s (-50) 20MB/s (-60) 16.6MB/s (-70)			5V+/-10%	Samples - Q4 95 Volume - Q1 96	N/A	P-SOJ-26/24pin 300 Mils; P-SOP II 26/24 pin 300 Mils JEDEC Standard
HYB 5116407 BJ/BJL-50/-60; HYB 5117407 BJ/BT-50/-60	Burst EDO (pipelined nibble) 6407 - 4k refresh 7407 - 2k refresh	16M	4Mx4	Min. R/W Cycle Time 84ns (-50) 104ns (-60) Burst Cycle Time 15ns (-50) 16.6ns (-60)	33MB/s (-50); 30MB/s (-60)			5V+/-10%	Samples - Q4 96; Volume - Ql 97	N/A	P-SOJ-26/24pin 300 mils; P-TSOP II 26/24 pin 300 Mils
HYB 5116165BSJ-50/-60/-70 HYB 5118165BSJ-50/-60/-70	EDO 6165 w/4k refresh 8165 w/ lk refresh	16M	lMxl6	Min. R/W Cycle Time 84ns (-50) 104ns (-60) 124ns (-70) H PM (EDO) Cycle time 20ns (-50) 25ns (-60) 30ns (-70)	100 MB/s (-50) 80MB/s (-60) 66MB/s (-70)			5V+/-10%	Samples - Now Volume - Q4 95	N/A	P-SOJ-42 pin 40OMils
HYB 3116167BSJ/BST-50 /-60 HYB 3118167BSJ/BST-50/-60	Burst EDO 6167 w/4k refresh 8167 w/lk refresh	16M	lMxl6	Min. R/W Cycle Time 84ns (-50) 94ns (-60) Burst (Pipelined Nibble) Cycle Time 15ns (-50); 16.6 ns (-60)	132MB/s (-50) 120MB/s (-60)			3.3V+/-0.3V S	Samples - Q3 97 Volume - Q497	N/A	P-SOJ-42 pin 400 Mils P-TSOP II 50/44 pin 40OMils JEDEC Standard
HYB 514267J-45/-50/-55/-60	EDO and BURST EDO	4M	256kxl6	Min.R/W Cycle Time l00ns (-45) 110ns (-50) 115ns (-55) 120ns (-60) Hyper Page Mode (EDO) Cycle time 20ns (-45) 22ns (-50) 25ns (-55) 27ns (-60)	1OOMB/s (-45) 90MB/s (-50) 80MB/s (-55) 75MB/s (-60) 133MB/s (-45) 117MB/s (-50) 100MB/s (-55) 90NM/s (-60)			5V+/-10%	Samples - Q1 98 Volume - Q2'98; N/A	N/A	P-SOJ-40 pin 400Mils JEDEC Standard
HYB 39Sl6l6O/800/400-10/-ll/-12/-13	SDRAM	16M	lMxl62Mx84Mx4	100MHz (-10) 9OMHz (-11) 83MHz (-12) 75MHz (-13)	200MB/s (lMxl6) 100MB/s (2Mx8) 50MB/s (4Mx4)			3.3V+/-0.3V.	Samples - Ql 97 Volume - Q2 97	N/A	xl6 in P-TSOP II-50 pins 40OMils x8/x4 in P-TSOP II -44 pins 400Mils JEDEC Standard
HYB 39M9320OX	Multibank DRAM	9Mbit	128kx32 208kx32 256kx32 288kx32	166/125/100/75MHz	664 MB/s			3.3V+/-0.3V	Samples - Q1 97; Volume - Q2 97	N/A	PQFP-128 pin PLCC-68 pin x32(x16 interface w/both clock edges used)

Texas Instruments, Inc. , Denver, Co., 800- 477-8924, Ext. 3037

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
TMS44409	EDO DRAM	4Mbit	1MX4	60ns 4OMHZ 20MB/s	20 MB/s			5 V	NOW		SOJ
TMS45169		4M	256KX16	60ns 4OMHZ	80MB/s			5V	1Q96		SOJ
TMS416169		16M	1MX16	60ns 4OMHZ	80 mB/S			5V	NOW		SOJ
TMS418169		16M	1MX16	60ns 4OMHZ	80MB/s			5V	NOW		SOJ
TMS426169		16M	1MX16	60ns 40MHZ	80MB/s			3.3V	4Q95		TSOPII
TMS428169		16M	1MX16	60 ns 40MHZ	80MB/s			3.3V	4Q95		SOJ
TMS416809		16M	2MX8	60ns 40MHZ	40mb/S			5V	2Q96		SOJTSOP II
TMS17809		16M	2MX8	60NS 40MHz	40MB/s			5V	1Q96		SOJ
TMS416409		16M	4MX4	60ns 40MHZ	20MB/s			5V	2Q96		SOJ
TMS417409		16M	4MX4	60ns 40MHZ	20MB/s			5V	2Q96		SOJ TSOP II
TMS426409		16M	4MX4	60ns 40MHZ	20MB/s			3.3V	2Q96		TSOP II
TMS427409		16M	4MX4	60ns 40MHZ	20MB/s			3.3V	2Q96		TSOP II
TMS464409		64M	16MX4	60ns 40 MH/z	20MB/s			3.3V	1997		SOJ TSOP II
TMS55lxx	VRAM	4M	256KXI6	60ns 55MHz	110MB/s			5V	Now		TSOP
TMS57lxx		4M	256KX16	60ns 55MHz	110MB/s			3.3V	TBD		TSOP
TMS626402	SDRAM	16M	2MX4X2 Banks	l0ns100 MHz	50MB/s			3.3V	2Q 96		TSOPII
TMS626802		16M	2MX8X2 Banks	10ns 100MHz	100MB/s			3.3V	2Q 96		TSOP II
TMS626162		16M	512KX16X2 Banks	12ns 83MHz	167MB/s			3.3V	1Q96		TSOP II

Toshiba America Electronic Components Irvine, Ca. 714-455-2000

Part Number	Type	Density	Organization	Clock Rate/ Access Time	Max. Bandwidth MB/sec	Active Current (mA)	Standby Current (mA)	Power Supply voltage	Availability	Price/ Quantity	Comments/Features
TC59S1604	SDRAM	16M	4M x4	10ns100MHz		100MB/ Sec		3.3V	Now	N/A	TSOP44 PIN
TC59S1608		16M	2M x8	10ns100MHz		100MB/ Sec		3.3V	Now	N/A	TSOP44 PIN
TC59S1616A		16M	1M x16	10ns100MHz		200MB/ Sec		3.3V	Dec. 95	N/A	TSOP50 PIN
TC59R1809	RDRAM	18M	2M x9	2ns500MHz		500MB/ Sec		3.3V	Now	N/A	SVP,SHP32 PIN
TC59R1608		16M	2M x8	2ns500MHz		500MB/ Sec		3.3V	1Q 96	N/A	SHP32 PIN
TC59R0808		8M	1M x8	2ns500MHz		500MB/ Sec		3.3V	2Q 96	N/A	SHP32 PIN
TC528257	VRAM	2M	256K x8	60ns40MHz		40MB/Sec		5V	Now	N/A	SOJ 40 PINTSOP 44PIN
TC528267		2M	256K x8	60ns40MHz		40MB/Sec		5V	Now	N/A	SOJ 40 PINTSOP 44 PIN